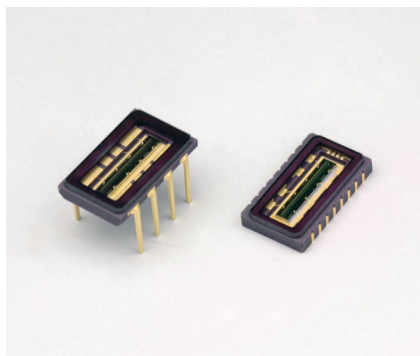


# CMOS linear image sensors



S9226 series

## Built-in timing generator and signal processing circuit; 3.3 V single supply operation

The S9226 series is a small CMOS linear image sensor designed for image input applications. The signal processing circuit has a charge amplifier with excellent input/output characteristics. Two package styles are provided: a DIP type and a surface mount type.

### Features

- Pixel pitch: 7.8  $\mu\text{m}$   
Pixel height: 125  $\mu\text{m}$
- 1024 pixels
- 3.3 V single power supply operation available
- High sensitivity, low dark current, low noise
- On-chip charge amplifier with excellent input/output characteristics
- Built-in timing generator allows operation with only start and clock pulse inputs.
- Video data rate: 200 kHz max.
- Spectral response range: 400 to 1000 nm
- Two package styles are provided:  
DIP (dual inline package) type: S9226-03  
Surface mount type: S9226-04

### Applications

- Analytical instruments
- Position detection
- Image reading

### Structure

Parameter	Specification	Unit
Number of pixels	1024	-
Pixel pitch	7.8	$\mu\text{m}$
Pixel height	125	$\mu\text{m}$
Photosensitive area length	7.9872	mm
Package	Ceramic	-
Window material	Borosilicate glass (Tempax)	-

### Absolute maximum ratings

Parameter	Symbol	Value	Unit
Supply voltage	Vdd	-0.3 to +6	V
Gain selection terminal voltage	Vg	-0.3 to +6	V
Clock pulse voltage	V(CLK)	-0.3 to +6	V
Start pulse voltage	V(ST)	-0.3 to +6	V
Operating temperature*1	Topr	-5 to +60	$^{\circ}\text{C}$
Storage temperature*1	Tstg	-10 to +70	$^{\circ}\text{C}$
Reflow soldering condition*2 *3	Tsol	Peak temperature 240 $^{\circ}\text{C}$ , 2 times (See P.8.)	-

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

\*1: No condensation

\*2: S9226-04

\*3: JEDEC level 5

### Recommended terminal voltage (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Vdd	3.3	5	5.25	V
Gain selection terminal voltage	Vg	-	0	-	V
		Vdd - 0.25	Vdd	Vdd + 0.25	V
Clock pulse voltage	V(CLK)	Vdd - 0.25	Vdd	Vdd + 0.25	V
		-	0	-	V
Start pulse voltage	V(ST)	Vdd - 0.25	Vdd	Vdd + 0.25	V
		-	0	-	V

### Electrical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5 V]

Parameter	Symbol	Min.	Typ.	Max.	Unit
Clock pulse frequency	f(CLK)	10 k	-	800 k	Hz
Video data rate	VR	-	f(CLK)/4	-	Hz
Power consumption	P	20	30	40	mW
Conversion efficiency	CE	-	3.2	-	$\mu\text{V}/e^-$
		-	1.6	-	
Output impedance*4	Zo	-	185	-	$\Omega$

### Electrical and optical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5 V]

Parameter	Symbol	Min.	Typ.	Max.	Unit
Spectral response range	$\lambda$	400 to 1000			nm
Peak sensitivity wavelength	$\lambda_p$	-	650	-	nm
Dark current	Id	-	5	50	fA
Dark output voltage*5	Vd	-	1	10	mV
		-	0.5	5	
Saturation output voltage*6	Vsat	2.2	3.2	-	V
Readout noise	Nr	-	1.4	2.2	mV rms
		-	0.7	1.1	
Offset output voltage	Vo	0.2	0.35	0.6	V
Photoresponse nonuniformity*7 *8	PRNU	-	-	±5	%

\*4: An increased current consumption at the video output terminal rises the sensor chip temperature causing an increased dark current. Connect a buffer amplifier for impedance conversion to the video output terminal so that the current flow is minimized.

Use a JFET or CMOS input, high-impedance input op amp as the buffer amplifier.

\*5: Integration time=10 ms

\*6: Voltage difference with respect to Vo

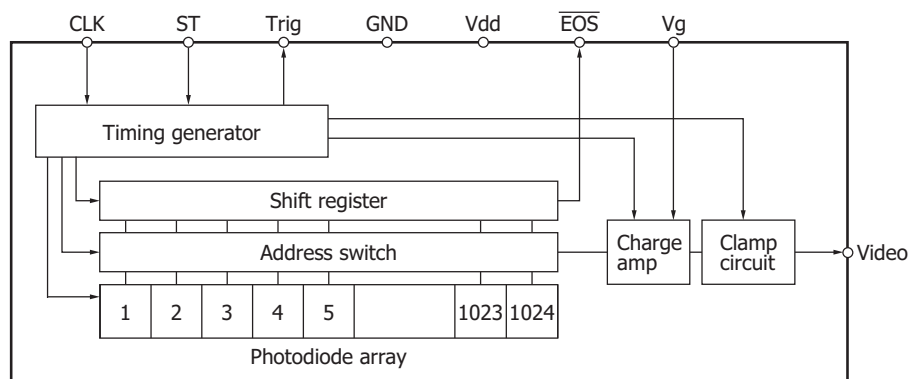
\*7: Photoresponse nonuniformity (PRNU) is the output nonuniformity that occurs when the entire photosensitive area is uniformly illuminated by light which is 50% of the saturation exposure level. PRNU is measured using 1022 pixels excluding the pixels at both ends, and is defined as follows:

$$\text{PRNU} = \Delta X / X \times 100 (\%)$$

X: average output of all pixels,  $\Delta X$ : difference between X and maximum or minimum output

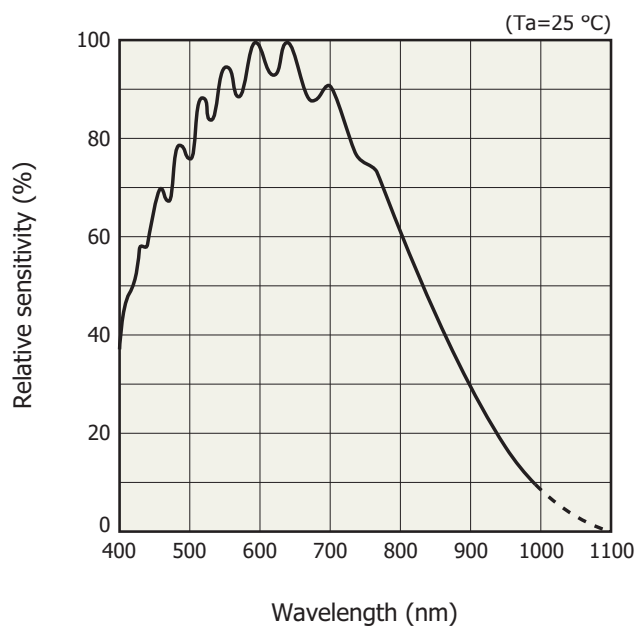
\*8: Measured with a tungsten lamp of 2856 K

### Block diagram



KMPDC0165EC

### Spectral response (typical example)



KMPDB0229EC

### Resolution

CTF: contrast transfer function

$$CTF = \frac{V_{WO} - V_{BO}}{V_W - V_B}$$

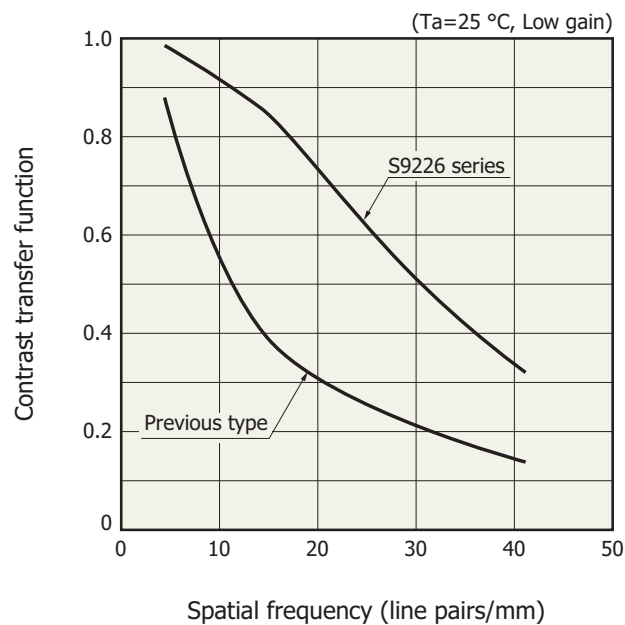
$V_{WO}$  : output white level

$V_{BO}$  : output black level

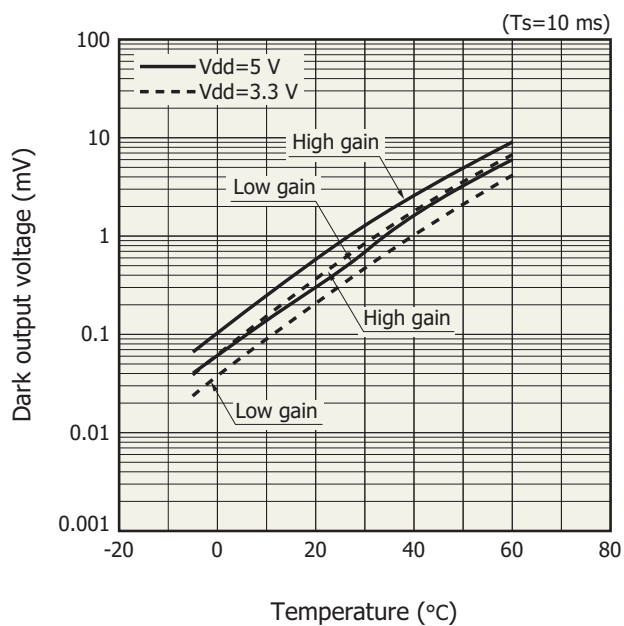
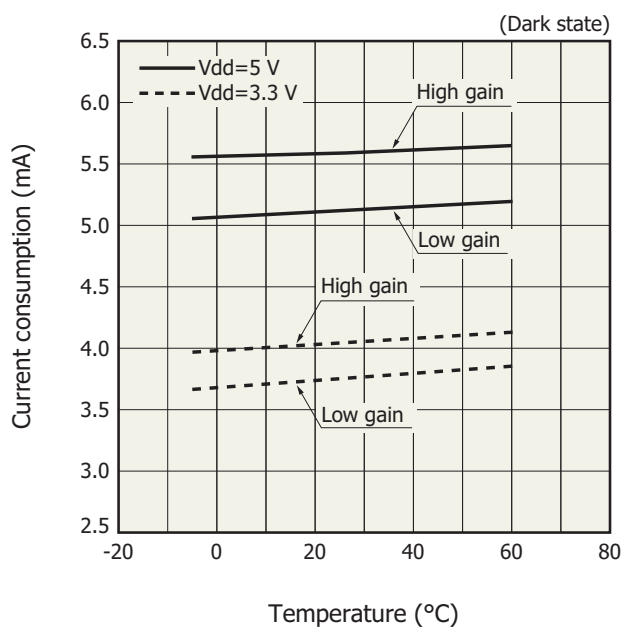
$V_W$  : output white level (when input pattern pulse width is wide)

$V_B$  : output black level (when input pattern pulse width is wide)

### Contrast transfer function vs. spatial frequency (typical example)

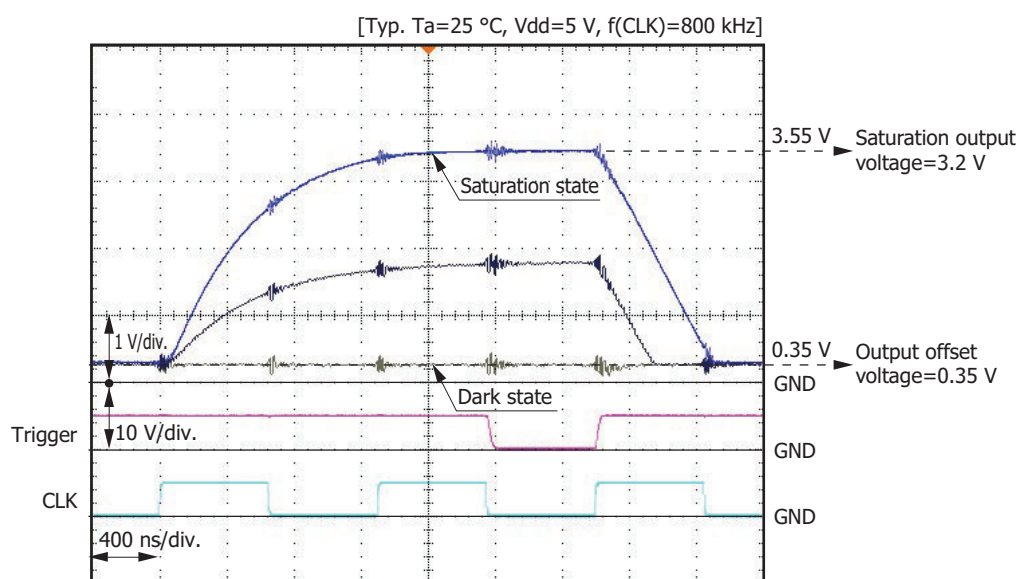


KMPDB0318EB

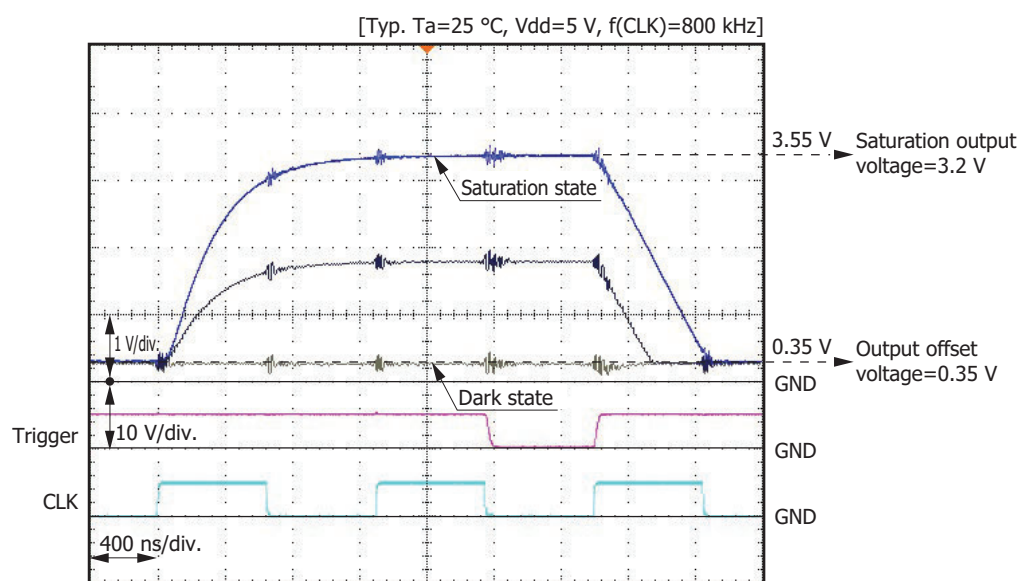
**Dark output voltage vs. temperature (typical example)****Current consumption vs. temperature (typical example)**

## Output waveform of one element

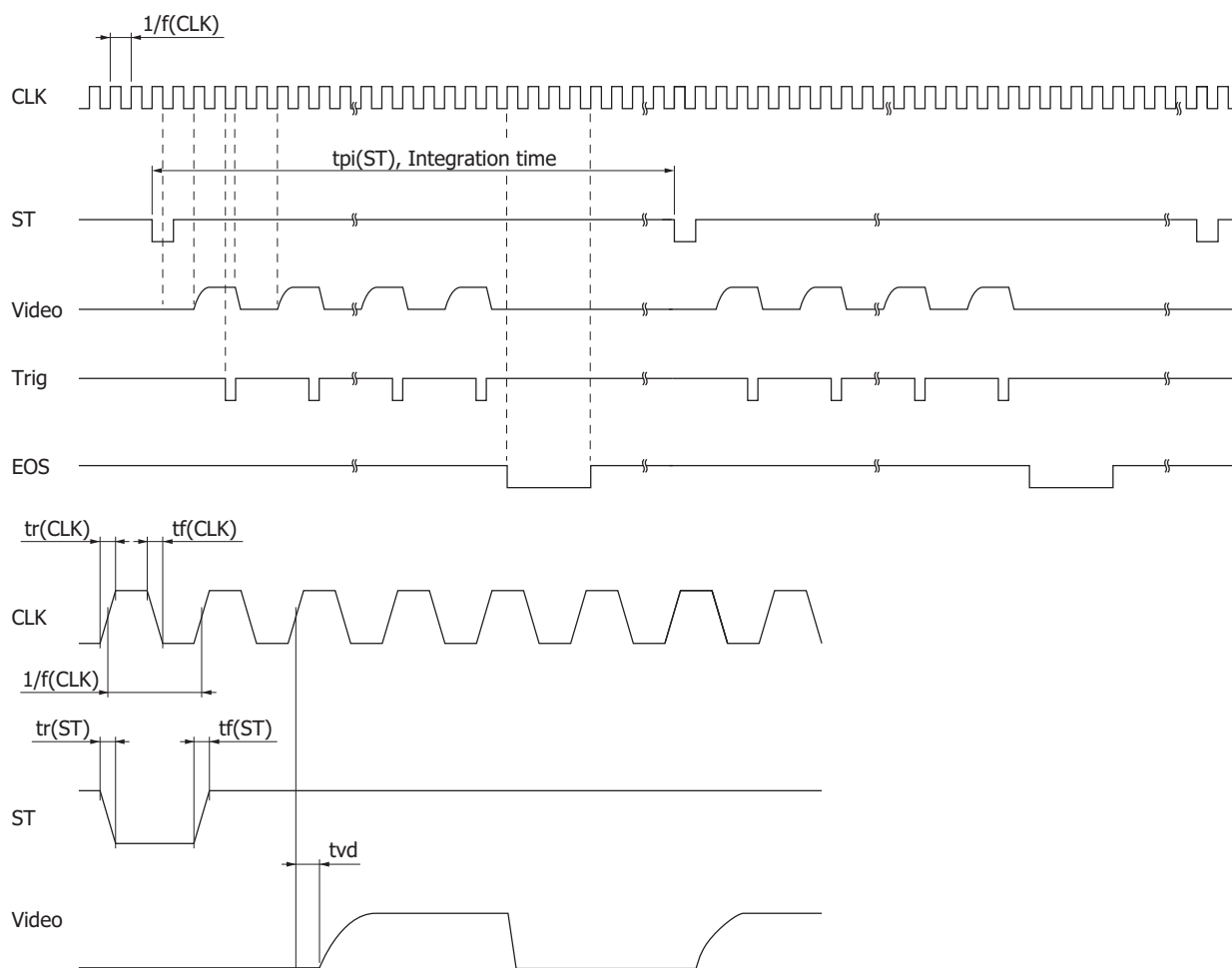
### High gain



### Low gain



## Timing chart



KMPDC0164EC

Parameter	Symbol	Min.	Typ.	Max.	Unit
Start pulse cycle	$t_{pi}(ST)$	$4104/f(CLK)$	-	-	s
Start pulse rise and fall times	$t_r(ST), t_f(ST)$	0	20	30	ns
Clock pulse duty ratio	-	40	50	60	%
Clock pulse rise and fall times	$t_r(CLK), t_f(CLK)$	0	20	30	ns
Video delay time* <sup>9</sup>	$t_{vd}$	10	20	30	ns

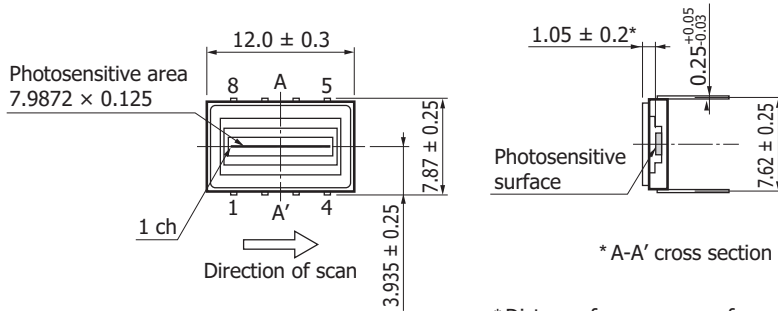
\*9:  $T_a=25\text{ }^{\circ}\text{C}$ ,  $V_{dd}=5\text{ V}$ ,  $V(CLK)=V(ST)=5\text{ V}$

Note: The CLK pulse should be set from high to low just once when the st pulse is low. The internal shift register starts operating at this timing.

The integration time is determined by the start pulse cycles. However, since the charge integration of each pixel is carried out between the signal readout of that pixel and the next signal readout of the same pixel, the start time of charge integration differs depending on each pixel. In addition, the next start pulse cannot be input until signal readout from all pixels is completed.

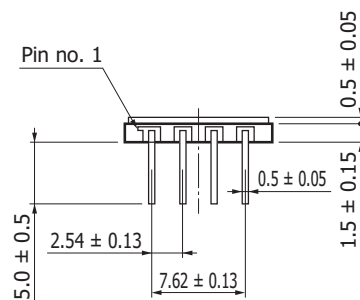
### Dimensional outlines (unit: mm)

S9226-03



\* A-A' cross section

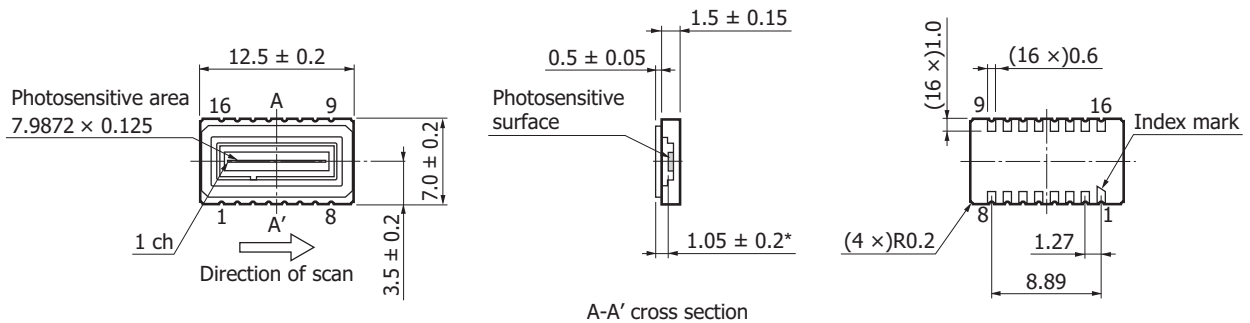
\* Distance from upper surface of window to photosensitive surface



KMPDA0172EF

Pin no.	Symbol	Pin name	Input/Output
1	GND	Ground	Input
2	CLK	Clock pulse	Input
3	Trig	Trigger pulse	Output
4	ST	Start pulse	Input
5	Vg	Gain selection voltage	Input
6	Video	Video output	Output
7	EOS	End of scan	Output
8	Vdd	Supply voltage	Input

S9226-04



A-A' cross section

\* Distance from upper surface of window to photosensitive surface

KMPDA0258EC

Pin no.	Symbol	Pin name	Input/Output	Pin no.	Symbol	Pin name	Input/Output
1	NC	No connection		9	NC	No connection	
2	NC	No connection		10	NC	No connection	
3	GND	Ground	Input	11	Vg	Gain selection voltage	Input
4	CLK	Clock pulse	Input	12	Video	Video output	Output
5	Trig	Trigger pulse	Output	13	EOS	End of scan	Output
6	ST	Start pulse	Input	14	Vdd	Supply voltage	Input
7	NC	No connection		15	NC	No connection	
8	NC	No connection		16	NC	No connection	

## Precautions

### (1) Electrostatic countermeasures

This device has a built-in protection circuit against static electrical charges. However, to prevent destroying the device with electrostatic charges, take countermeasures such as grounding yourself, the workbench and tools to prevent static discharges. Also protect this device from surge voltages which might be caused by peripheral equipment.

### (2) Light input window

If the incident window is contaminated or scratched, the output uniformity will deteriorate considerably, so care should be taken in handling the window. Avoid touching it with bare hands.

The window surface should be cleaned before using the device. If dry cloth or dry cotton swab is used to rub the window surface, static electricity may be generated, and therefore this practice should be avoided. Use soft cloth, cotton swab or soft paper moistened with ethyl alcohol to wipe off dirt and foreign matter on the window surface.

### (3) Soldering

To prevent damaging the device during soldering, take precautions to prevent excessive soldering temperatures and times. Soldering should be performed within 5 seconds at a soldering temperature below 260 °C.

### (4) Reflow soldering (S9226-04)

Soldering conditions may differ depending on the board size, reflow furnace, etc. Check the conditions before soldering. A sudden temperature rise and cooling may be the cause of trouble, so make sure that the temperature change is within 4 °C per second.

The bonding portion between the ceramic base and the glass may discolor after reflow soldering, but this has no adverse effects on the hermetic sealing of the product.

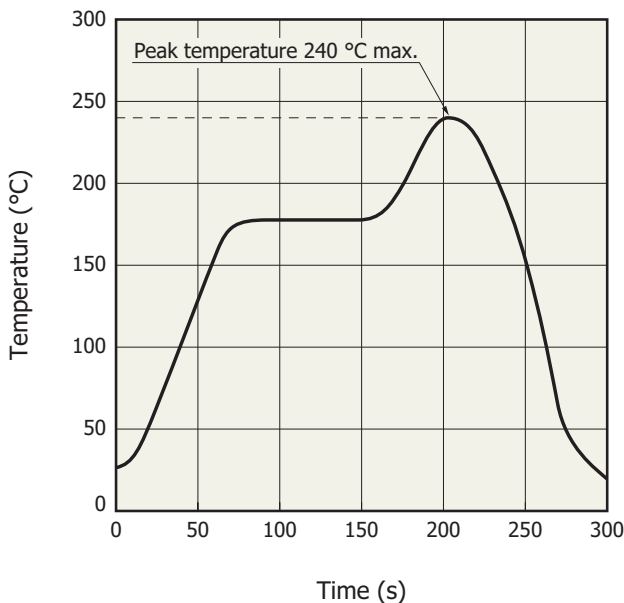
### (5) Operating and storage environments

Always observe the rated temperature range when handling the device. Operating or storing the device at an excessively high temperature and humidity may cause variations in performance characteristics and must be avoided.

### (6) UV exposure

This product is not designed to prevent deterioration of characteristics caused by UV exposure, so do not expose it to UV light.

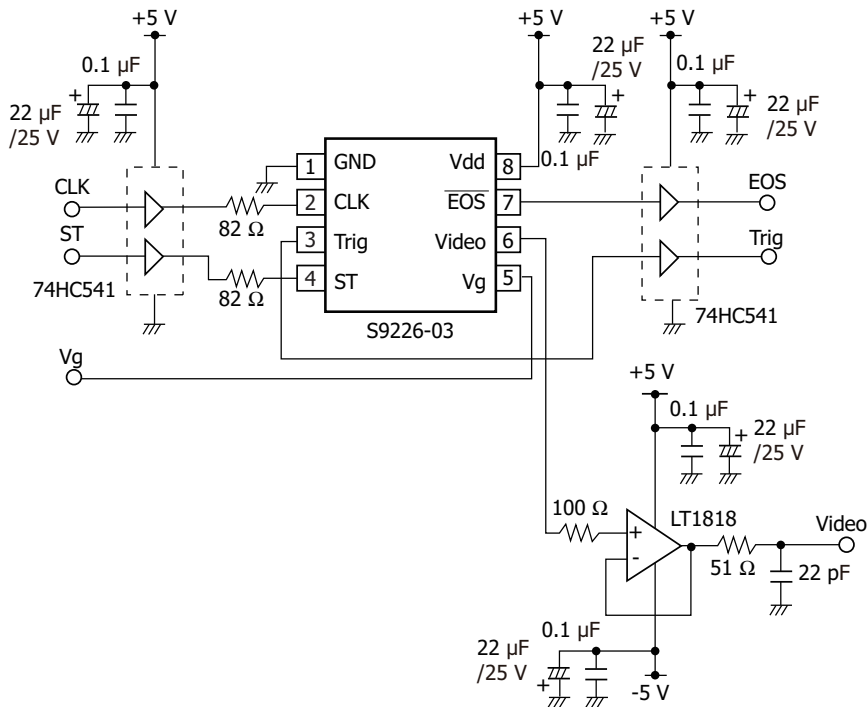
## Recommended temperature profile reflow soldering (S9226-04)



KAPDB0169EA



### Application circuit example (S9226-03)\*10



KMPDC0416EA

\*10: The S9226-04 has a different pin connections, but uses the same circuit.

### Related information

[www.hamamatsu.com/sp/ssd/doc\\_en.html](http://www.hamamatsu.com/sp/ssd/doc_en.html)

#### Precautions

- Notice
- Image sensors/Precautions
- Surface mount type products/Precautions

Information described in this material is current as of January, 2014.

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# HAMAMATSU

[www.hamamatsu.com](http://www.hamamatsu.com)

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 8152-375-0, Fax: (49) 8152-265-8

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trappu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Thorshamnsgatan 35 16440 Kista, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1 int. 6, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741

China: Hamamatsu Photonics (China) Co., Ltd.: 1201 Tower B, Jiaming Center, No.27 Dongsanhuan Beilu, Chaoyang District, Beijing 100020, China, Telephone: (86) 10-6586-6006, Fax: (86) 10-6586-2866